N-Channel 150-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- Fast switching speed

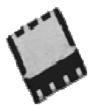
Typical Applications:

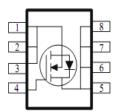
- PoE PSE and PD Circuits
- LED Inverter Circuits
- 48V-Input DC/DC Conversion Circuits

PRODUCT SUMMARY				
V _{DS} (V)	$V_{DS}(V)$ $r_{DS(on)}(m\Omega)$			
150	160 @ V _{GS} = 10V	4.6		
130	$180 @ V_{GS} = 5.5V$	4.4		









ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Units				
Drain-Source Voltage			150	V			
Gate-Source Voltage	V_{GS}	±20	V				
Continuous Drain Current ^a	T _A =25°C	I _D	4.6				
Continuous Diain Current	T _A =70°C	טי	3.7	Α			
Pulsed Drain Current ^b		I _{DM}	30				
Continuous Source Current (Diode Conduction) a	I _S	4.4	Α				
Power Dissipation ^a	T _A =25°C	P _D	5	W			
rower dissipation	T _A =70°C	' D	3.2	V V			
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
Maximum Junction-to-Ambient	Steady State		65	C/VV			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

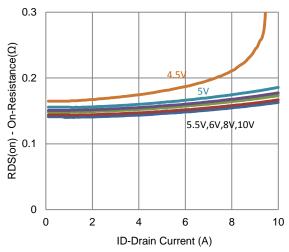
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lane	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	7			Α	
Drain Source On Besistance a	r	$V_{GS} = 10 \text{ V}, I_D = 3.5 \text{ A}$			160	mΩ	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = 5.5 \text{ V}, I_D = 2.8 \text{ A}$			180	11152	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 3.5 \text{ A}$		11		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.2 \text{ A}, V_{GS} = 0 \text{ V}$		0.78		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 75 \text{ V}, V_{GS} = 5.5 \text{ V},$		12			
Gate-Source Charge	Q_{gs}	$I_{DS} = 73 \text{ V}, \text{ V}_{GS} = 3.3 \text{ V},$ $I_{D} = 3.5 \text{ A}$		5.7		nC	
Gate-Drain Charge	Q_{gd}	1B = 3.5 A		4.7			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 75 \text{ V}, R_1 = 21.5 \Omega,$		10			
Rise Time	t _r	$V_{DS} = 75 \text{ V}, K_L - 21.3 \Omega,$ $I_D = 3.5 \text{ A},$		8		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		29		ns	
Fall Time	t _f	V GEN = 10 V, 1 (GEN = 0.12		9			
Input Capacitance	C _{iss}			1158			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		81		pF	
Reverse Transfer Capacitance	C_{rss}			45			

Notes

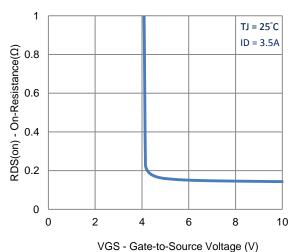
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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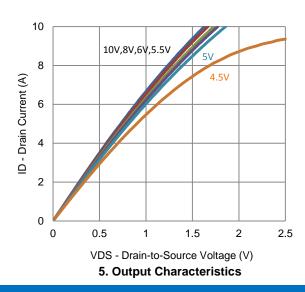
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage



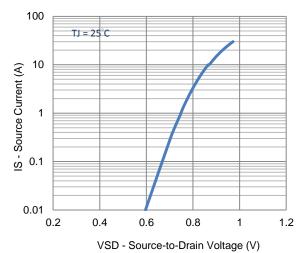
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TJ = 25°C

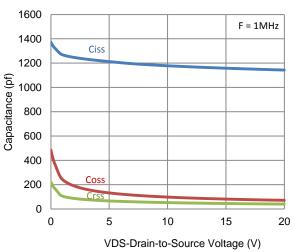
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2. Transfer Characteristics

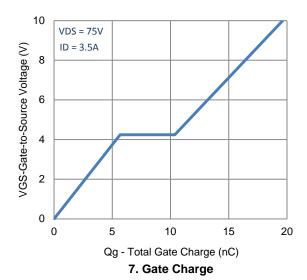


4. Drain-to-Source Forward Voltage



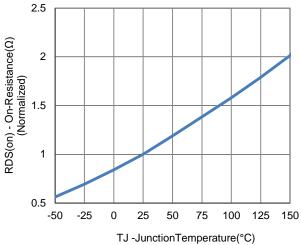
6. Capacitance

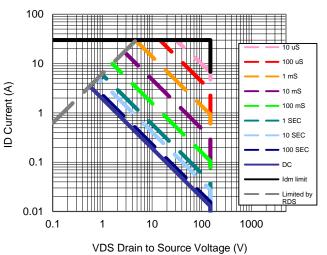
Typical Electrical Characteristics

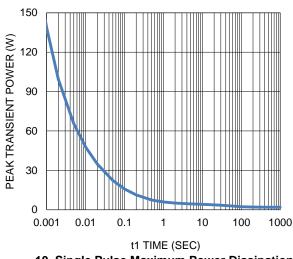


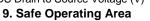
TJ -JunctionTemperature(°C)

8. Normalized On-Resistance Vs
Junction Temperature

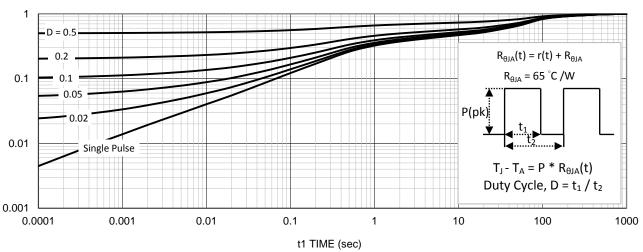






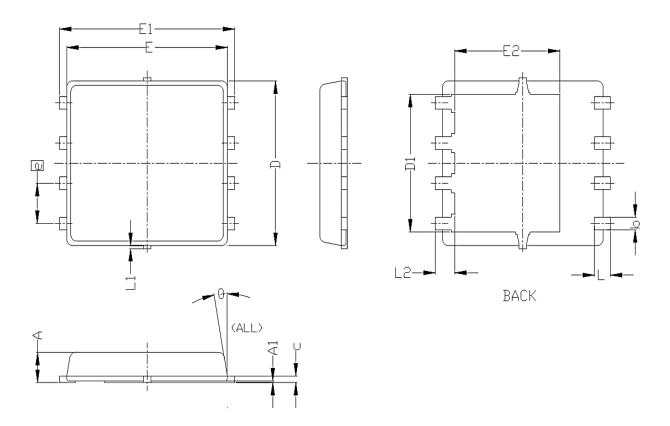


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS		DIMENSIONS IN INCHES				
STMBULS	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.85	0.95	1.00	0.033	0.037	0.039	
A1	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
с	0.15	0. 20	0. 25	0.006	0.008	0.010	
D	5. 20 BSC			0. 205 BSC			
D1	4. 35 BSC			0. 171 BSC			
Е	5, 55 BSC			0, 219 BSC			
E1	6. 05 BSC		0. 238 BSC				
E2	3. 62 BSC		0. 143 BSC				
e	1. 27 BSC			0.050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	